# 29th AACGE Western Section
## Conference on Crystal Growth & Epitaxy

**Stanford Sierra Camp, Fallen Leaf Lake, CA**

**June 7-11, 2026**

# Welcome to
# Stanford Sierra Conference Center

The following information will help you during your stay at our lakeside retreat and enjoy your visit to the fullest!

The best way to keep in touch with the office and home is to bring a laptop with wireless capability. Our wireless network is available throughout the camp, including lodge rooms, meeting rooms, and common areas in the main lodge, as well as in the cabins.

Cell service is spotty and inconsistent at Fallen Leaf Lake so plan to be without cell reception during your stay.

You can receive phone messages at 530-541-1244 and receive faxes at 530-541-2212.

Registration, registration payment, and registration concerns can be emailed to aacg@comcast.net. Visit www.crystalgrowth.org to register and/or pay online.

We post phone messages and faxes on the guest message board across from the office. Check out time on departure day is 10:00.

Our website is www.stanfordsierra.com.

Morgan Marshall
Sales & Marketing Director (530) 541-1244 ext.125
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# Conference Contacts

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# 2026 Sponsors

AACGE-West would like to gratefully acknowledge funding from:

https://www.crystalgrowth.org

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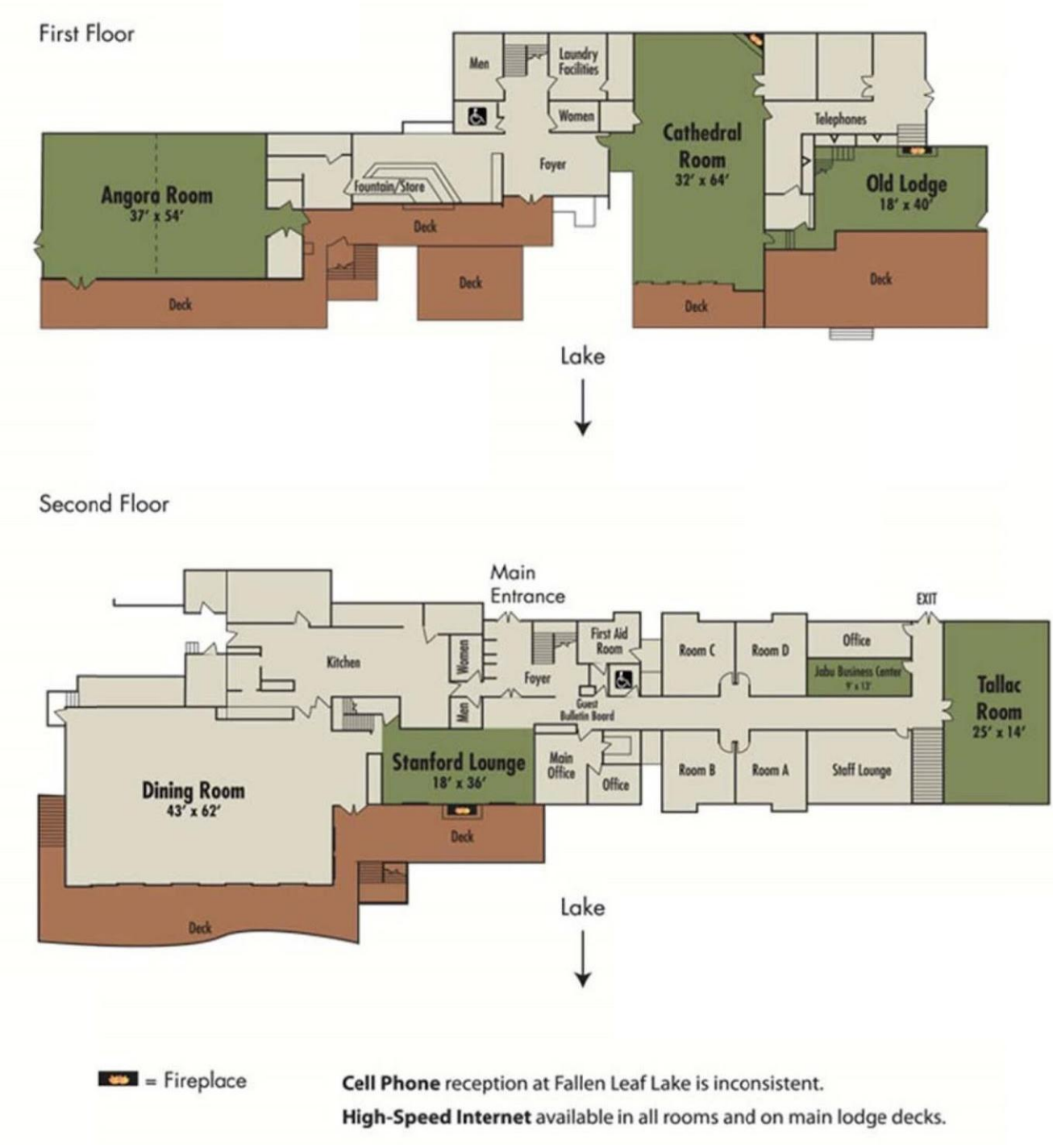
# Main Lodge Facilities



# Program Guide

## Sunday, June 7, 2026

| | | |
|---|---|---|
| Stanford Lounge | 15:00 – 18:00 | Camp Check-in & Conference Registration |
| Old Lodge Deck | 16:30 – 18:00 | Welcome Reception |
| Dining Room | 18:00 – 19:30 | Dinner |
| Cathedral Room | 19:30 – 21:00 | Epitaxial Crystal Growth |

## Monday, June 8, 2026

| | | |
|---|---|---|
| Dining Room | 7:30 – 9:00 | Breakfast |
| Cathedral Room | 9:30 – 10:30 | Fundamentals of Crystallization |
| | 10:30 – 11:00 | Break |
| Cathedral Room | 11:00 – 12:00 | Fundamentals of Crystallization |
| Dining Room | 12:00 – 13:30 | Lunch |
| | 13:30 – 16:00 | Camp Activities Unscheduled Time |
| Angora Room | 16:00 – 18:00 | Posters |
| Dining Room | 18:00 – 19:30 | Dinner |
| Cathedral Room | 19:30 – 20:15 | Plenary Lecture I |
| Cathedral Room | 20:20 – 21:10 | Colloidal Crystallization |

## Tuesday, June 7, 2026

| | | |
|---|---|---|
| Dining Room | 7:30 – 9:00 | Breakfast |
| Cathedral Room | 9:30 – 10:30 | Session |
| | 10:30 – 11:00 | Break |
| Cathedral Room | 11:00 – 11:40 | AI/ML for Crystal Growth |
| Deck | 11:45 – 12:00 | Meeting Photo |
| Dining Room | 12:00 – 13:30 | Lunch |
| | 13:30 – 16:00 | Camp Activities Unscheduled Time |
| Angora Room | 16:00 – 18:00 | Podcast |
| Dining Room | 18:00 – 19:30 | Dinner |
| Cathedral Room | 19:30 – 20:15 | Plenary Lecture II |
| Cathedral Room | 20:20 – 21:10 | Colloidal Crystallization |

## Wednesday, June 8, 2026

| | | |
|---|---|---|
| Dining Room | 7:30 – 9:00 | Breakfast |
| Cathedral Room | 9:30 – 10:30 | Biological & Biomimetic Materials |
| | 10:30 – 11:00 | Break |
| Cathedral Room | 11:00 – 12:10 | Biological & Biomimetic Materials |
| Dining Room | 12:00 – 13:30 | Lunch |
| | 13:30 – 16:00 | Camp Activities Unscheduled Time |
| Angora Room | 16:00 – 17:00 | Student Panel |
| Dining Room | 17:30 – 19:30 | Dinner |
| Cathedral Room | 19:30 – 21:10 | Epitaxial Crystal Growth |

## Thursday, June 9, 2026

| | | |
|---|---|---|
| Dining Room | 7:30 – 9:00 | Breakfast |
| Cathedral Room | 9:30 – 10:30 | Fundamentals of Crystallization |
| | 10:30 – 11:00 | Break |
| Cathedral Room | 11:00 – 12:00 | Fundamentals of Crystallization |
| Dining Room | 12:00 – 13:30 | Lunch &<br>Camp Departure |

# Program

## Sunday, June 7, 2026

| | |
|---|---|
| 19:30 – 21:00 | Epitaxial Crystal Growth I |
| Cathedral Room | |
| Chair: | Ganesh Balakrishnan |

| | |
|---|---|
| 19:30 – 20:00 | Atomic-scale characterization of growth and overgrowth of III-V semiconductor nanostructures. **– Invited –**<br>Rainer Timm, Lund University |
| 20:00 – 20:20 | Strain- and instability-driven lateral compositional modulation of compound semiconductors – can we make use of it?<br>Sang Han, University of New Mexico |
| 20:20 – 20:40 | Engineering epitaxial quantum dots for telecommunication wavelength single photon emitter applications.<br>Ganesh Balakrishnan, University of New Mexico |
| 20:40 – 21:00 | Epitaxial oxidation sequences in titanium and scandium nanoislands.<br>Pip Knight, Massachusetts Institute of Technology |

## Monday, June 8, 2026

| | |
|---|---|
| 9:00 – 10:30 | Fundamentals of Crystallization I |
| Cathedral Room | |
| Chair: | Kristen Fichthorn |
| 9:00 – 9:30 | Two-step crystallization and polymorph selection in 3-chloromandelic acid. **– Invited –**<br>Michael Gruenwald, University of Utah |
| 9:30 – 9:50 | Molecular origins of competing nucleation pathways in complex environments.<br>Nikhil Rampal, Lawrence Livermore National Laboratory |
| 9:50 – 10:10 | Observations on the oxygen ion behavior in high temperature solutions.<br>Vincent Fratello, Retired |
| 10:10 – 10:30 | Unprecedented packing polymorphism of oxindole: an exploration inspired by crystal structure prediction.<br>Xiaolong Zhu, Merck |
| 10:30 – 11:00 | Break |
| 11:00 – 11:20 | Replacement of the Ostwald rule of stages to predict the sequence of appearance of crystal polymorphs.<br>Peter Vekilov, University of Houston |
| 11:20 – 11:40 | Dynamic studies of material properties at the Lawrence Livermore National Laboratory.<br>Thomas Lockard, Lawrence Livermore National Laboratory |
| 11:40 – 12:00 | Iron acquisition and mineral transformation by cyanobacteria living in extreme environments.<br>David Kisailus, University of California Irvine |

## Monday, June 8, 2026

16:00 – 18:00 Poster Session
Angora Room
Chair: Jong Seto

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## Monday, June 8, 2026

19:30 – 21:10 Plenary Lecture & Colloidal Crystallization I
Cathedral Room
Chair: Talid Sinno

19:30 – 20:15 Dislocation and 2D nucleation mechanisms in large organic and inorganic crystals grown from solution. **– Plenary I –**
Natalia Zaitseva, Lawrence Livermore National Laboratory

20:20 – 20:50 Cracking colloidal crystallization: classical nucleation and growth with a twist. **– Invited I –**
Benjamin Rogers, Brandeis University

20:50 – 21:10 FFT-based analysis of quantum dot superlattices.
Ken Seungmin Hong, Brown University

## Tuesday, June 9, 2026

| | |
|---|---|
| 9:00 – 10:30 | Artificial Intelligence & Machine Learning for Crystal Growth |
| Cathedral Room | |
| Chair: | Katie Colbaugh & Moneesh Upmanyu |
| 9:00 – 9:30 | High-fidelity atomistic simulations of alloy solidification. **– Invited –**<br>Rodrigo Freitas, Massachusetts Institute of Technology |
| 9:30 – 9:50 | Data-driven coarse-graining: Discovering continuum scale models from atomistic simulations.<br>Amit Samanta, Lawrence Livermore National Laboratory |
| 9:50 – 10:10 | Predicting antimalarial activity modes in hematin crystallization using a priori machine learning.<br>Hariharan Annadurai, University of Houston |
| 10:10 – 10:30 | Identifying useful nanocrystal morphologies using advanced sampling techniques and machine learning.<br>Kirsten Fichthorm, Penn State University |
| 10:30 – 11:00 | Break |
| 11:00 – 11:20 | A comparative study of PIML and general ML/AI approaches for industrial crystal growth.<br>Katie Colbaugh, Leucite |
| 11:20 – 11:40 | TBD.<br>Timofey Frolov, Lawrence Livermore National Laboratory |

## Tuesday, June 9, 2026

| | |
|---|---|
| 11:45 – 12:00 | Group Photo |
| Outside Deck | |
| Chair: | Luis Zepeda-Ruiz |
| 11:45 – 12:00 | All attendees invited for our group photo. |

## Tuesday, June 9, 2026

16:00 – 18:00 Podcast
Angora Room
Chair: Dhruvaite Upmanyu

16:00 – 18:00 Everyone is encouraged to be interviewed.

## Tuesday, June 9, 2026

19:30 – 21:10 Plenary Lecture & Colloidal Crystallization II
Cathedral Room
Chair: Talid Sinno

19:30 – 20:15 Self-assembly and crystallization at protein-inorganic interfaces.
**– Plenary II –**
James DeYoreo, Pacific Northwest National Laboratory

20:20 – 20:50 Computational self-assembly of diverse colloidal crystal and cluster structures. **– Invited –**
Julia Dshemuchadse, Cornell University

20:50 – 21:10 Can hydrodynamic interactions explain anomalously fast nucleation in weakly-supersaturated colloidal fluids?
Talid Sinno, University of Pennsylvania

## Wednesday, June 10, 2026

| | |
|---|---|
| 9:00 – 10:30 | Biological & Biomimetic Materials |
| Cathedral Room | |
| Chair: | Jong Seto |

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|---|---|
| 9:00 – 9:30 | Control over crystallization from metastable mineral precursors by manipulation of polyelectrolytes. **– Invited –**<br>Thomas Schroeder, North Carolina State University |
| 9:30 – 10:00 | Mesoporous frameworks engineered from crystallizable collagen-mimetic peptide amphiphiles. **– Invited –**<br>Andrea Merg, University of California Merced |
| 10:00 – 10:20 | Template-directed toxicity sink: molecular mechanisms of lithium-mediated Aβ42 oligomer–fibril interconversion.<br>Radhika Sunil Menon, University of Houston |
| 10:20 – 10:40 | Organization and complexation of an extracellular matrix protein with Ca2+ ions.<br>Jong Seto, Arizona State University |
| 10:30 – 11:00 | Break |
| 11:00 – 11:30 | High-resolution structural studies at the interface of biology and materials science. **– Invited –**<br>Brent Nannega, Arizona State University. |
| 11:30 – 11:50 | The structural landscape of amyloid-β oligomerization by high-speed AFM.<br>Nghia Nguyen, University of Houston. |
| 11:50 – 12:10 | Clustering of Zn in ectopic biominerals at the biological interfaces in the temporomandibular joint and the kidney.<br>Sunita Ho, University of California San Francisco |

## Wednesday, June 10, 2026

16:00 – 17:30 Poster Award Talks & Career Panel Discussion
Angora Room
Chair: Luis Zepeda-Ruiz

16:00 – 16:15 Poster Awards talks.

16:15 – 17:30 Career Panel Discussion.

## Wednesday, June 10, 2026

19:30 – 21:00 Epitaxial Crystal Growth II
Cathedral Room
Chair: Ganesh Balakrishnan

19:30 – 20:00 Modeling SiGe quantum dot variability induced by interface disorder reconstructed from multi-perspective microscopy. **– Invited –**
Ezra Bussman, Sandia National Laboratory

20:00 – 20:30 Oxide thin films for electronic and optical applications. **– Invited –**
Wilfrid Prellier, Centre National de la Recherche Scientifique (CNRS)

20:30 – 20:50 Analytical x-ray solutions for thin film and wafer analysis.
Destiny Lopez, Malvern Panalytical

20:50 – 21:10 Correlating epitaxial growth and electronic properties of crystalline high-k metal oxides on 2D materials.
Rishabh Kothari, Massachusetts Institute of Technology

## Thursday, June 11, 2026

| | |
|---|---|
| 9:00 – 10:30 | Fundamentals of Crystallization II |
| Cathedral Room | |
| Chair: | Kristen Fichthorn |

| | |
|---|---|
| 9:00 – 9:30 | From colloidal nano building blocks to higher order architectures.<br>**– Invited –**<br>Ou Chen, Brown University |
| 9:30 – 9:50 | The Impact of Wadsley defects and cation disorder on improving $MoNb_{12}O_{33}$ diffusion.<br>Cristopher Sturgill, University of South Carolina |
| 9:50 – 10:10 | Solvent-dependent relative stability of crystal forms.<br>Rohith Pulluri, University of Houston |
| 10:10 – 10:30 | Coupling catalyst activity and degradation: modeling oxygen evolution reaction with surface dissolution on IrO2(110).<br>Rhys Bunting, Lawrence Livermore National Laboratory |
| 10:30 – 11:00 | Break |
| 11:00 – 11:20 | Atomic-scale insights into calcite dissolution kinetics in nonstoichiometric solutions and the role of $Mg^{2+}$ ions.<br>Shuhong Song, Pacific Northwest National Laboratory |
| 11:20 – 11:40 | Crystallization entropy: constituents and contributions to crystal form stability.<br>Alejandro Veliz, University of Houston |
| 11:40 – 12:00 | TBD.<br>Moneesh Upmanyu, Northeastern University |

# Abstracts

**Sunday, June 7, 2026**
**19:30 – 21:00 Epitaxial Crystal Growth**

Atomic-scale characterization of growth and overgrowth of III-V semiconductor.
Rainer Timm, Lund University

III-V semiconductor nanostructures, with their superior charge carrier mobility and a direct and tunable band gap, are promising for next generation devices in electronics, photonics, energy harvesting, and quantum information. They offer a large flexibility in forming material, doping, or crystal phase heterostructures. III-V nanowires are especially interesting both from an application and crystal growth perspective, as they combine a complex interplay of lateral and radial growth, can crystallize in structures that are not stable in bulk, and can act as templates for growth of novel nanostructures.
We are using scanning tunnelling microscopy and spectroscopy (STM/S) as well as synchrotron-based X-ray photoelectron spectroscopy (XPS) in various setups for studying growth, atomic structure, and electronic properties of III-V semiconductor nanostructures at the atomic scale. Here, I will show STM/S results highlighting different stages of nanowire growth and overgrowth, where we map nanowires across axial heterostructures between different materials, doping level, or different crystal phase, and correlate the surface structure and local electronic properties, down to quantum size effects. Nanowire crystal phase heterostructures can act as templates for radial overgrowth with atomic-scale control, enabling the growth of novel types of nanostructures monitored by STM: Figure 1 shows the surface of a GaAs nanowire which has been exposed to Bi atoms, resulting in the self-selective growth of well-ordered GaBi 1D and 2D nanostructures on the surface of the wurtzite segment, while only individual Bi atoms or small Bi clusters were incorporated in the zincblende surface.
Bismuth incorporation in III-V semiconductor surfaces also leads to interesting growth phenomena upon 2D film growth. I will show examples of self-limiting Bi growth on InSb(111)B and of a honeycomb surface structure of Bi atoms on GaAs(111)B, which – in contrast to conventional Bismuthene – form strong covalent bonds to the As atoms of the underlying GaAs, but are only weakly bond to each other. These structures are promising for non-trivial topological behavior at room temperature and large Rashba splitting.

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Strain- and instability-driven lateral compositional modulation of compound semiconductors - can we make use of it?
Sang Han, University of New Mexico

Phase instability and interatomic diffusion in epitaxially grown III–V semiconductors are generally associated with materials degradation and eventual device failure. Here, we explore whether these same processes can instead be used to produce lateral compositional modulation and bandgap engineering. Using GaAsSb/InP as a model system, we examine the evolution of a lattice-matched GaAsSb epilayer during high-temperature annealing. Rather than conventional spinodal decomposition alone, we observe pronounced migration of Sb from the GaAsSb epilayer into the InP substrate and counter-diffusion of P

from the substrate into the epilayer. This intermixing produces InSb-rich tips and facets of pyramidal nanostructures together with InGaAsP regions that replace the original GaAsSb layer. High-resolution x-ray diffraction, Raman spectroscopy, scanning transmission electron microscopy, and energy-dispersive x-ray spectroscopy collectively indicate that the transformation is driven by liquid-assisted phase separation associated with transient molten InSb, providing an alternative mechanism to previously proposed solid-state spinodal decomposition. By applying external biaxial strain through stressed SiNx capping layers, the net strain during annealing can be tuned from compressive to tensile. A critical strain appears to exist that strongly alters the resulting morphology, producing a transition from deeply penetrating intermixed domains to laterally confined InSb/InGaAsP layers while substantially slowing the kinetics of degradation. These results demonstrate that phase instability and interdiffusion can be directed by strain and may provide a route to controlled lateral compositional modulation in compound semiconductors.

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Engineering epitaxial quantum dots for telecommunication wavelength single photon emitter applications.
Ganesh Balakrishnan, University of New Mexico

Epitaxial III–V quantum dots (QDs) are promising candidates for single-photon emitters, but conventional InAs/GaAs systems are limited in achieving emission at telecommunication wavelengths. This work explores alternative epitaxial growth pathways using arsenide and antimonide material systems to extend emission beyond 1.3 μm while maintaining control over morphology and optical properties.

InAs growth on InP substrates is investigated as a reduced lattice-mismatch system that enables thicker planar growth prior to three-dimensional island formation. On InP (001), anisotropic surface diffusion leads to elongated quantum dash structures, whereas growth on InP (311)B suppresses this anisotropy and promotes the formation of isolated, symmetric quantum dots exhibiting single-dot emission. Growth parameters such as coverage and growth rate are shown to critically influence the dimensional transition and dot density.

GaSb quantum dot formation on GaAs is also examined under varying stoichiometric conditions. Sb-rich growth results in strain-relaxed islands mediated by misfit dislocation arrays, while group-III-rich conditions favor coherent Stranski–Krastanov growth. Interdiffusion during capping can further modify dot morphology, leading to ring-like structures and altered optical behavior.

These results highlight the role of epitaxial growth conditions, substrate orientation, and strain management in tailoring quantum dot structure and emission properties. The study provides insight into growth mechanisms enabling long-wavelength QDs and supports their integration into quantum photonic devices.

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Epitaxial oxidation sequences in titanium and scandium nanoislands.
Pip Knight, Massachusetts Institute of Technology

Understanding epitaxial oxidation processes is crucial to many areas of nanoscience that require control of surface structure or utilize oxidation as a synthetic step to a final nanostructure. For example, in industrial chemical reactions catalyzed by metal nanoparticles, the surface structure of the catalytic nanoparticle depends on the gas environment and is crucial to surface catalytic activity1. Meanwhile in microelectronics, oxidized metal seed layers are proposed to enable the growth of homogeneous gate

oxide films on challenging substrates like 2D materials2, so controlling the phase and epitaxy of the oxide seed is essential for controlling these same properties of the film. However, detailed studies of epitaxial oxidation are challenging for more reactive metals because without an ultra-high vacuum (UHV) growth and imaging environment, it is not possible to capture the first stages of oxidation, such as suboxide formation. Furthermore, a detailed study of epitaxial oxidation sequences requires epitaxial, single crystalline metal as a starting material, ideally in a well-defined morphology.

In our work, we aim to understand the oxidation sequences of reactive metals. To do this, we grow flat, epitaxial nanoislands and films of the metals on suspended multilayer graphene (Gr) substrates to use as the starting point for oxidation studies. We focus on the hexagonal close-packed metals titanium (Ti) and scandium (Sc), which are both promising high k dielectric oxides for microelectronics3,4. The metals are grown by electron beam deposition in UHV, then transferred in the same vacuum system to our UHV transmission electron microscope (TEM) where the phase transformations are conducted in situ. By making movies of the phase transformation, we can understand morphology changes and use in situ electron diffraction to track the formation of new crystallographic phases. We find that the sequence of daughter phases that form in each case are epitaxial, and we examine the crystallographic relationships between the sequence of suboxide phases to understand the the atomic scale reaction pathway. We also indirectly probe the relative diffusivities of oxygen compared with the metal for each case by observing with in situ TEM whether the nanoscale Kirkendall effect occurs. Finally, we extend our study of in situ metal-gas reactions by discussing prospects for nitride formation reactions.

References:

1. Yokosawa, Tadahiro, Frans D. Tichelaar, and Henny W. Zandbergen. "In-Situ TEM on Epitaxial and Non-Epitaxial Oxidation of Pd and Reduction of PdO at P= 0.2–0.7 bar and T= 20–650° C." European Journal of Inorganic Chemistry 2016.19 (2016): 3094-3102.

2. Kim, Hoijoon, et al. "Ultrathin monolithic HfO2 formed by Hf-seeded atomic layer deposition on MoS2: Film characteristics and its transistor application." Thin Solid Films 673 (2019): 112-118.

3. Kim, Taikyu, et al. "Atomic layer growth of rutile TiO2 films with ultrahigh dielectric constants via crystal orientation engineering." ACS Applied Materials & Interfaces 16.26 (2024): 33877-33884.

4. Lebedev, M. S., et al. "Optical properties and charge transport of textured Sc2O3 thin films obtained by atomic layer deposition." Applied Surface Science 478 (2019): 690-698.

**Monday, June 8, 2026**
**9:00 – 11:40 Fundamentals of Crystallization I**

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**Monday, June 8, 2026**
**19:30 – 20:15 Plenary I**

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**Monday, June 8, 2026**
**20:20 – 21:10 Colloidal Crystallization I**

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**Tuesday, June 9, 2026**
**9:00 – 11:40 Artificial Intelligence $ Machine Learning for Crystal Growth**

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**Tuesday, June 9, 2026**
**19:30 – 20:15 Plenary II**

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**Tuesday, June 9, 2026**
**20:20 – 21:10 Colloidal Crystallization II**

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**Wednesday, June 10, 2026**
**9:00 – 11:40 Biological & Biomimetic Materials**

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**Wednesday, June 10, 2026**
**19:30 – 21:10 Epitaxial Crystal Growth II**

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**Thursday, June 11, 2026**
**9:00 – 11:40 Fundamentals of Crystallization II**

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## ACCGE-25 • OMVPE-23

Colorado Springs, Colorado, USA

2027

**25th American Conference on Crystal Growth (ACCGE-25)**

*and*

**23rd US Workshop on Organometallic Vapor Phase Epitaxy (OMVPE-23)**

*to be held in*
**Colorado Springs, Colorado, USA**
*at the Cheyenne Mountain Resort*

**JULY 25, 2027 – JULY 29, 2027**

### ABOUT THE CONFERENCE

This biennial conference continues the tradition of being the confluence of all things crystal growth and epitaxy – growth methods (melt, vapor, solution, etc.), material type (semiconductors, biological, oxides, etc.), dimensionality (bulk, thin films, 2D, nano) and properties (optical, electronic, optoelectronic, ferroelectric, etc.) – providing a forum to bring together scientists, engineers, and researchers from academia, industry, and government laboratories from US and around the world to discuss the latest advances. The conference is an ideal venue for young researchers - postdocs, graduate and undergraduate students - to learn and seek career opportunities in the crystal growth field.

**Inspiring Location**
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**Connect & Collaborate**
Network with leaders and peers in crystal growth.

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Visit the conference website for updates, registration, and more details.

### SCAN TO LEARN MORE

www.accge25-omvpe23.org